



# PJF4NA65A

## 650V N-Channel MOSFET

**Voltage**

**650 V**

**Current**

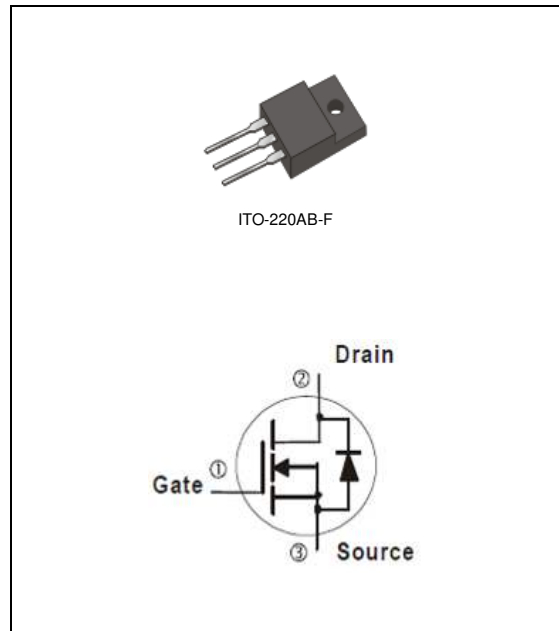
**4 A**

### Features

- $R_{DS(ON)}, V_{GS}@10V, I_D@2A < 2.7\Omega$
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std.  
(Halogen Free)

### Mechanical Data

- Case : ITO-220AB-F Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.068 ounces, 2 grams



### Maximum Ratings and Thermal Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	ITO-220AB-F	UNITS
Drain-Source Voltage	$V_{DS}$	650	V
Gate-Source Voltage	$V_{GS}$	$\pm 30$	V
Continuous Drain Current	$I_D$	4	A
Pulsed Drain Current	$I_{DM}$	16	A
Single Pulse Avalanche Energy <sup>(Note 1)</sup>	$E_{AS}$	202	mJ
Power Dissipation	$T_C=25^\circ\text{C}$	33	W
	Derate above $25^\circ\text{C}$	0.26	W/ $^\circ\text{C}$
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~150	$^\circ\text{C}$
Typical Thermal resistance			$^\circ\text{C}/\text{W}$
- Junction to Case	$R_{\theta JC}$	3.79	
- Junction to Ambient	$R_{\theta JA}$	120	

- Limited only By Maximum Junction Temperature



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## Electrical Characteristics ( $T_A=25^\circ\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
<b>Static</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	650	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2	3	4	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=2A$	-	2.5	2.7	$\Omega$
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=650V, V_{GS}=0V$	-	-	1.0	$\mu A$
Gate-Source Leakage Current	$I_{GSS}$	$V_{GS}=\pm 30V, V_{DS}=0V$	-	-	$\pm 100$	nA
Diode Forward Voltage	$V_{SD}$	$I_S=4A, V_{GS}=0V$	-	0.76	1.4	V
<b>Dynamic</b> (Note 4)						
Total Gate Charge	$Q_g$	$V_{DS}=520V, I_D=4A,$ $V_{GS}=10V$ (Note 2,3)	-	18	-	nC
Gate-Source Charge	$Q_{gs}$		-	3.3	-	
Gate-Drain Charge	$Q_{gd}$		-	8.3	-	
Input Capacitance	$C_{iss}$	$V_{DS}=25V, V_{GS}=0V,$ $f=1.0\text{MHz}$	-	555	-	pF
Output Capacitance	$C_{oss}$		-	55.4	-	
Reverse Transfer Capacitance	$C_{rss}$		-	2.41	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=325V, I_D=4A,$ $R_G=25\Omega$ (Note 2,3)	-	11	-	ns
Turn-On Rise Time	$t_r$		-	25	-	
Turn-Off Delay Time	$t_{d(off)}$		-	52	-	
Turn-Off Fall Time	$t_f$		-	29	-	
<b>Drain-Source Diode</b>						
Maximum Continuous Drain-Source Diode Forward Current	$I_S$	---	-	-	4	A
Maximum Pulsed Drain-Source Diode Forward Current	$I_{SM}$	---	-	-	16	A
Reverse Recovery Time	$t_{rr}$	$V_{GS}=0V, I_S=4A$	-	266	-	ns
Reverse Recovery Charge	$Q_{rr}$	$di_F/dt=100A/\mu s$ (Note 2)	-	2.24	-	$\mu C$

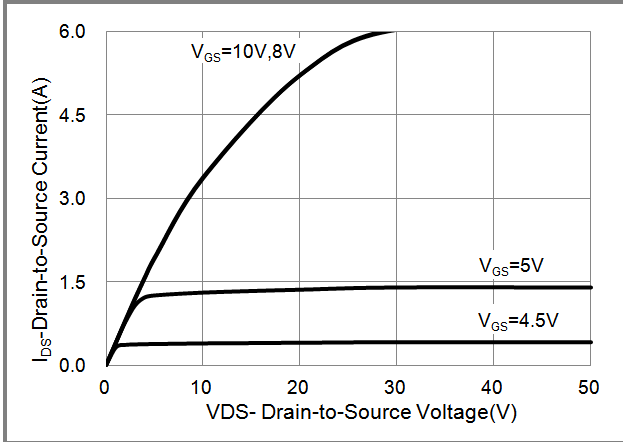
NOTES :

1.  $L=30\text{mH}, I_{AS}=3.6A, V_{DD}=50V, R_G=25\text{ohm}$ , Starting  $T_J=25^\circ\text{C}$
2. Pulse width  $\leq 300\mu s$ , Duty cycle  $\leq 2\%$
3. Essentially independent of operating temperature typical characteristics.
4. Guaranteed by design, not subject to production testing

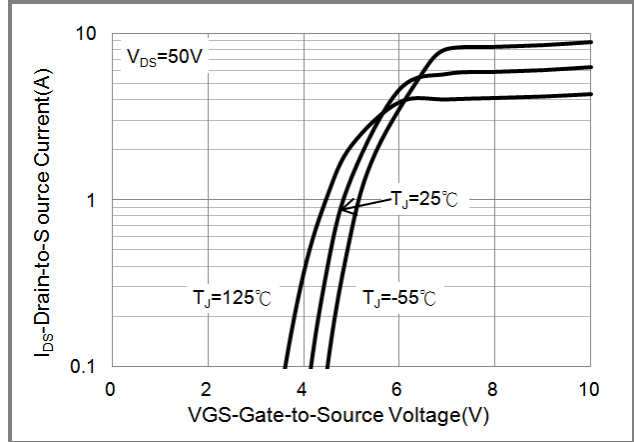


# PJF4NA65A

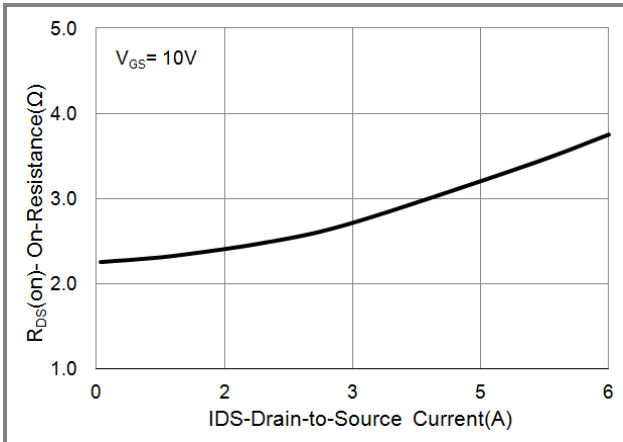
## TYPICAL CHARACTERISTIC CURVES



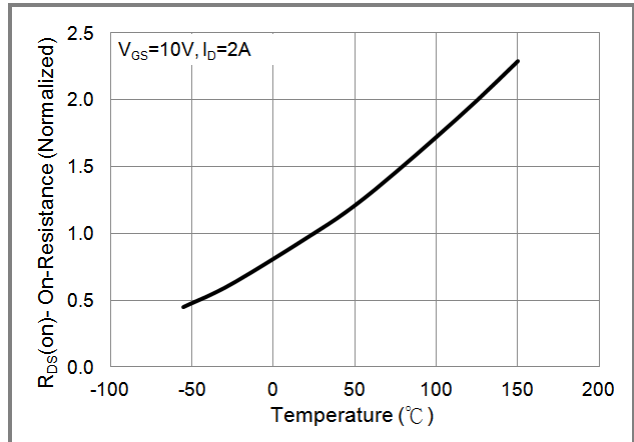
**Fig.1 Output Characteristics**



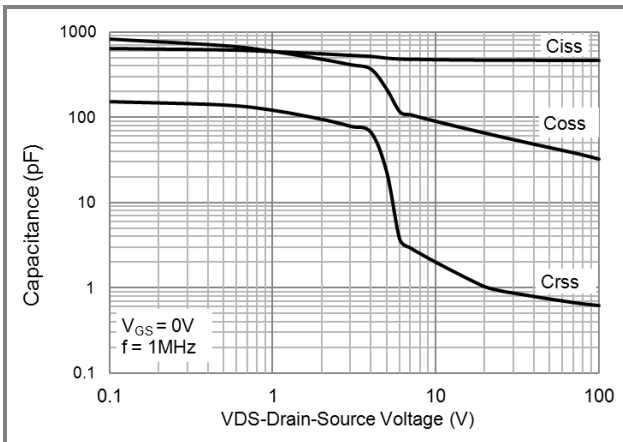
**Fig.2 Transfer Characteristics**



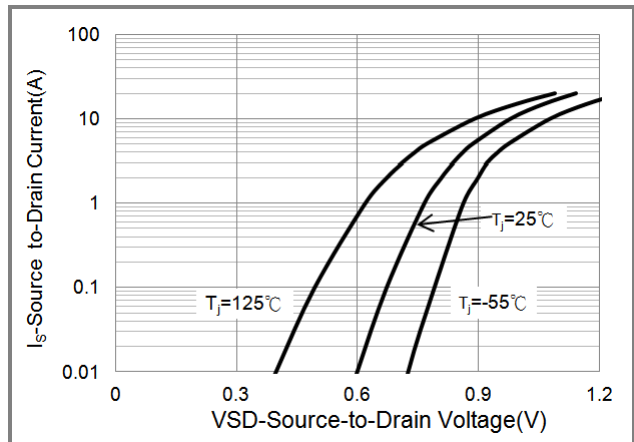
**Fig.3 On-Resistance vs. Drain Current**



**Fig.4 On-Resistance vs. Junction Temperature**



**Fig.5 Capacitance vs. Drain-Source Voltage**



**Fig.6 Source-Drain Diode Forward Voltage**



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## TYPICAL CHARACTERISTIC CURVES

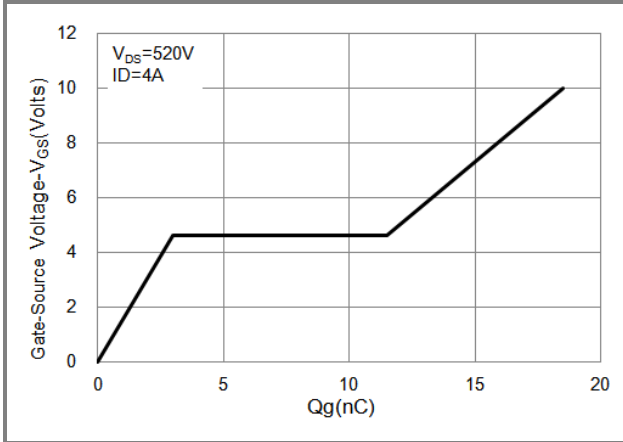


Fig.7 Gate Charge

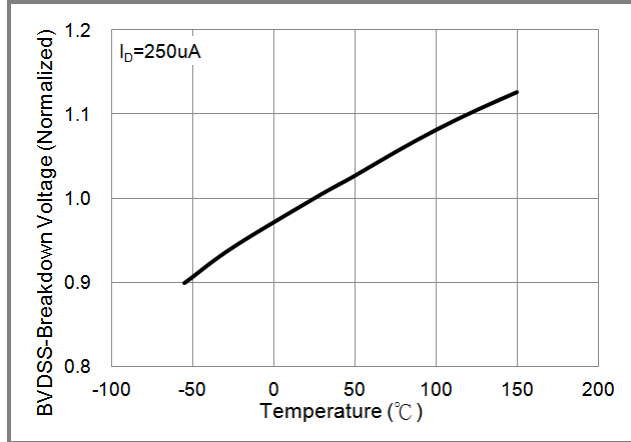


Fig.8  $BV_{DSS}$  vs. Junction Temperature

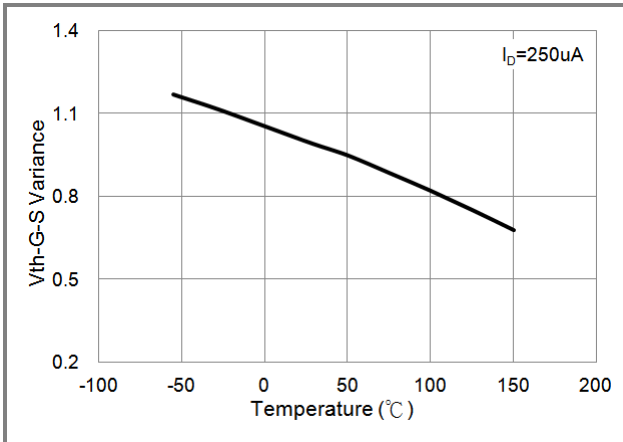


Fig.9 Threshold Voltage Variation with Temperature

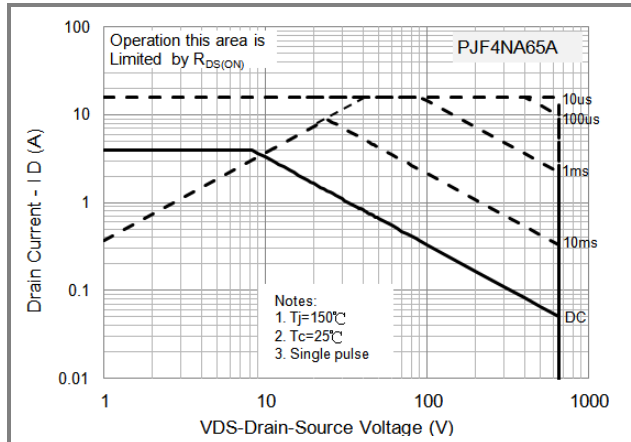


Fig.10 Maximum Safe Operating Area

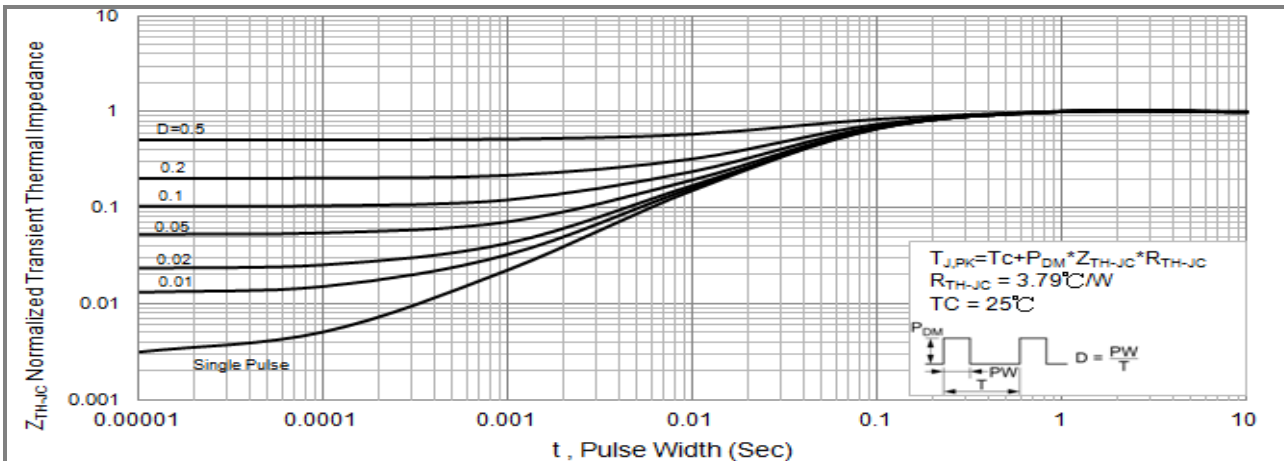
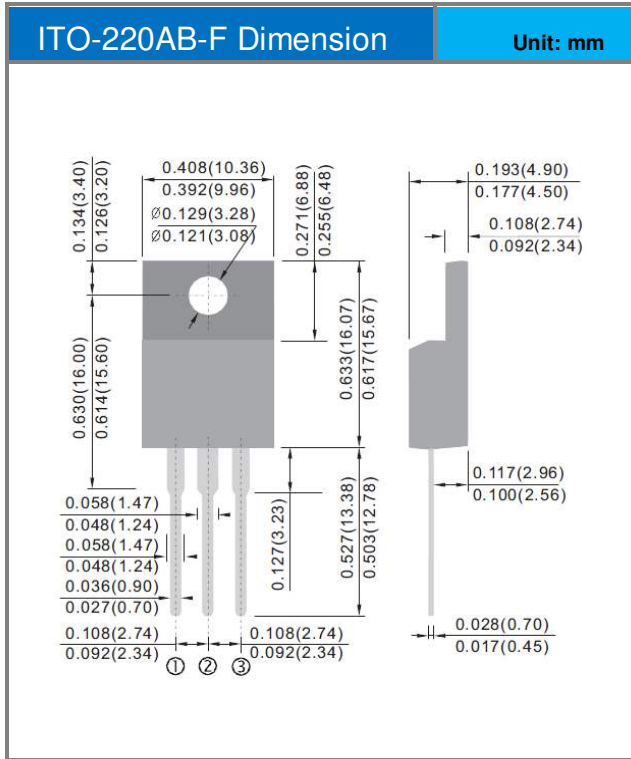


Fig.11 PJF4NA65A Normalized Transient Thermal Impedance vs. Pulse Width



# PJF4NA65A

## Packaging Information





# PJF4NA65A

## PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJF4NA65A_T0_00001	ITO-220AB-F	50pcs / Tube	F4NA65A	Halogen free



## PJF4NA65A

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